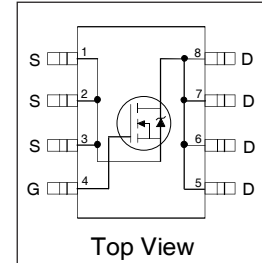


DEVICE CHARACTERISTICS^⑤

	IRF7809AV
$R_{DS(on)}$	7.0m Ω
Q_G	41nC
Q_{SW}	14nC
Q_{OSS}	30nC

HEXFET[®] Power MOSFET



Features

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



Benefits

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7809AVPbF-1	SO-8	Tube/Bulk	95	IRF7809AVPbF-1
		Tape and Reel	4000	IRF7809AVTRPbF-1

Absolute Maximum Ratings

Parameter	Symbol	IRF7809A V	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain or Source Current ($V_{GS} \geq 4.5V$)	I_D	13.3	A
		14.6	
Pulsed Drain Current ^①	I_{DM}	100	
Power Dissipation	P_D	2.5	W
		3.0	
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$
Continuous Source Current (Body Diode)	I_S	2.5	A
Pulsed Source Current ^①	I_{SM}	50	

Thermal Resistance

Parameter		Max.	Units
Maximum Junction-to-Ambient ^③	$R_{\theta JA}$	50	$^{\circ}C/W$
Maximum Junction-to-Lead	$R_{\theta JL}$	20	$^{\circ}C/W$

Electrical Characteristics

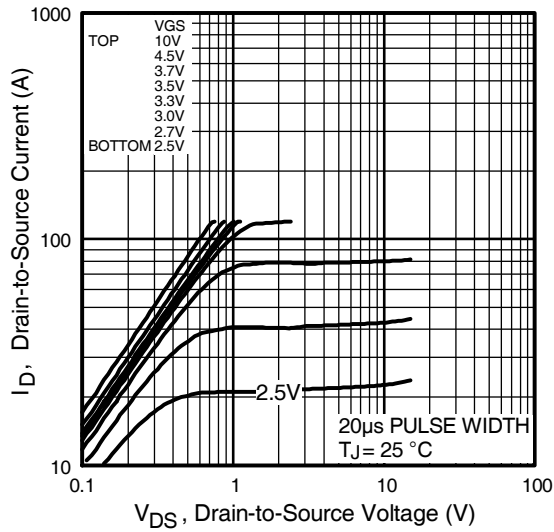
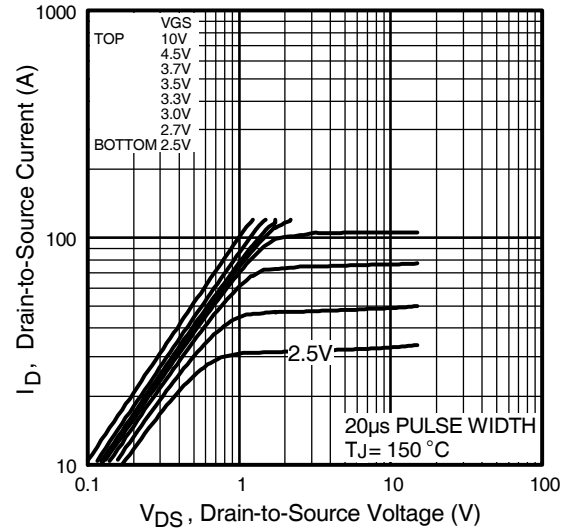
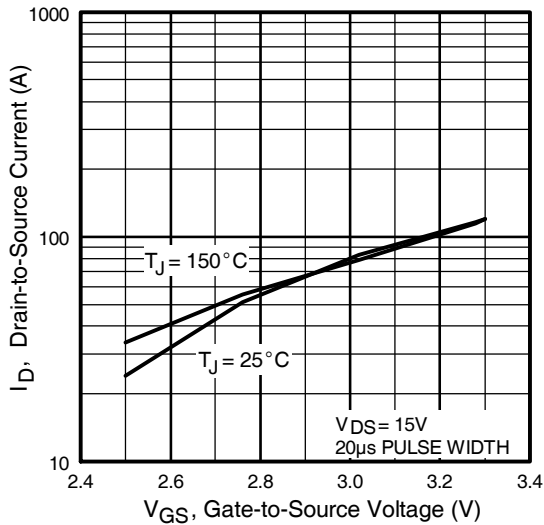
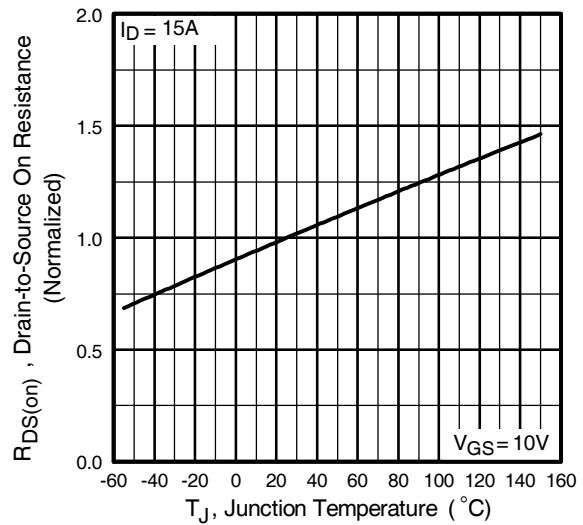
Parameter		Min	Typ	Max	Units	Conditions
Drain-to-Source Breakdown Voltage	BV_{DSS}	30	–	–	V	$V_{GS} = 0V, I_D = 250\mu A$
Static Drain-Source on Resistance	$R_{DS(on)}$		7.0	9.0	m Ω	$V_{GS} = 4.5V, I_D = 15A$ ②
Gate Threshold Voltage	$V_{GS(th)}$	1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Drain-Source Leakage Current	I_{DSS}			30	μA	$V_{DS} = 24V, V_{GS} = 0$
				150		$V_{DS} = 24V, V_{GS} = 0,$ $T_j = 100^\circ C$
Gate-Source Leakage Current*	I_{GSS}			± 100	nA	$V_{GS} = \pm 12V$
Total Gate Chg Cont FET	Q_G		41	62	nC	$V_{GS}=5V, I_D=15A, V_{DS}=20V$
Total Gate Chg Sync FET	Q_G		36	54		$V_{GS} = 5V, V_{DS} < 100mV$
Pre-Vth Gate-Source Charge	Q_{GS1}		7.0			$V_{DS} = 20V, I_D = 15A$
Post-Vth Gate-Source Charge	Q_{GS2}		2.3			
Gate to Drain Charge	Q_{GD}		12			$I_D=15A, V_{DS}=16V$
Switch Chg($Q_{GS2} + Q_{GD}$)	Q_{SW}		14	21		
Output Charge*	Q_{OSS}		30	45		$V_{DS} = 16V, V_{GS} = 0$
Gate Resistance	R_G		1.5	3.0	Ω	
Turn-on Delay Time	$t_{d(on)}$		14		ns	$V_{DD} = 16V, I_D = 15A$
Rise Time	t_r		36			$V_{GS} = 5V$
Turn-off Delay Time	$t_{d(off)}$		96			Clamped Inductive Load
Fall Time	t_f		10			
Input Capacitance	C_{iss}	–	3780	–	pF	$V_{DS} = 16V, V_{GS} = 0$
Output Capacitance	C_{oss}	–	1060	–		
Reverse Transfer Capacitance	C_{rss}	–	–	130		

Source-Drain Rating & Characteristics

Parameter		Min	Typ	Max	Units	Conditions
Diode Forward Voltage*	V_{SD}			1.3	V	$I_S = 15A$ ②, $V_{GS} = 0V$
Reverse Recovery Charge④	Q_{rr}		120		nC	$di/dt \sim 700A/\mu s$ $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$
Reverse Recovery Charge (with Parallel Schottky)④	$Q_{rr(s)}$		150		nC	$di/dt = 700A/\mu s$ (with 10BQ040) $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 400 \mu s$; duty cycle $\leq 2\%$.
- ③ When mounted on 1 inch square copper board, $t < 10$ sec.
- ④ Typ = measured - Q_{OSS}
- ⑤ Typical values measured at $V_{GS} = 4.5V, I_F = 15A$.


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

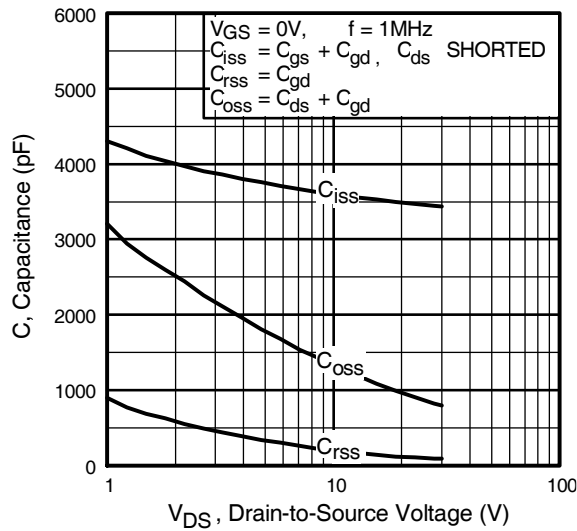


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

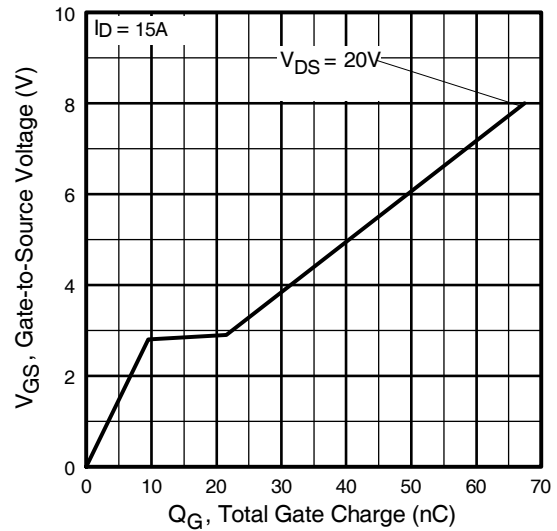


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

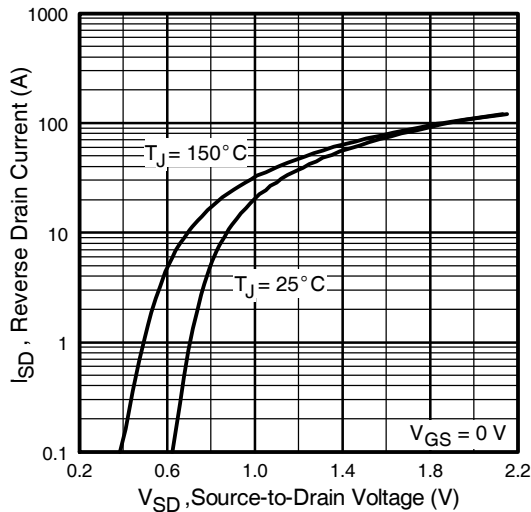


Fig 7. Typical Source-Drain Diode Forward Voltage

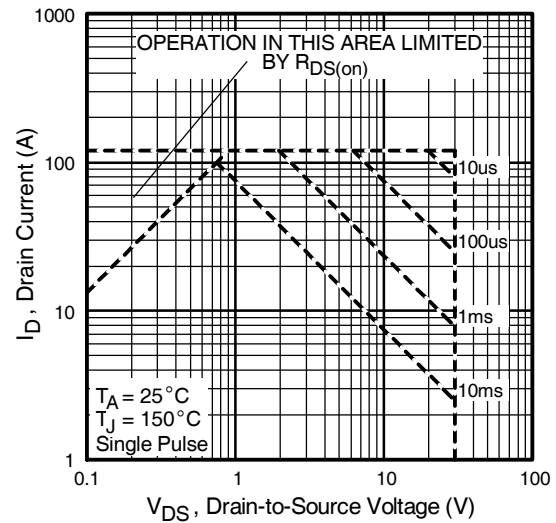


Fig 8. Maximum Safe Operating Area

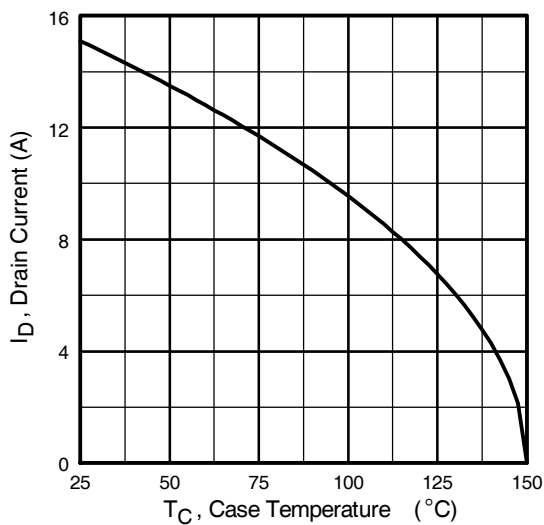


Fig 9. Maximum Drain Current Vs. Case Temperature

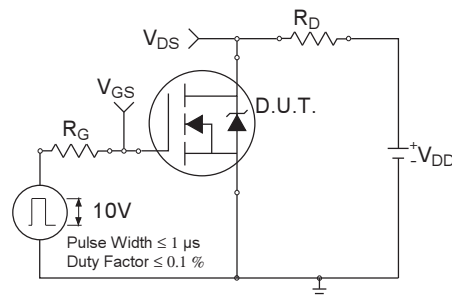


Fig 10a. Switching Time Test Circuit

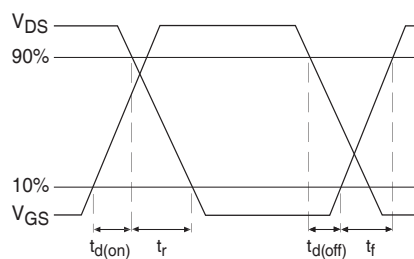


Fig 10b. Switching Time Waveforms

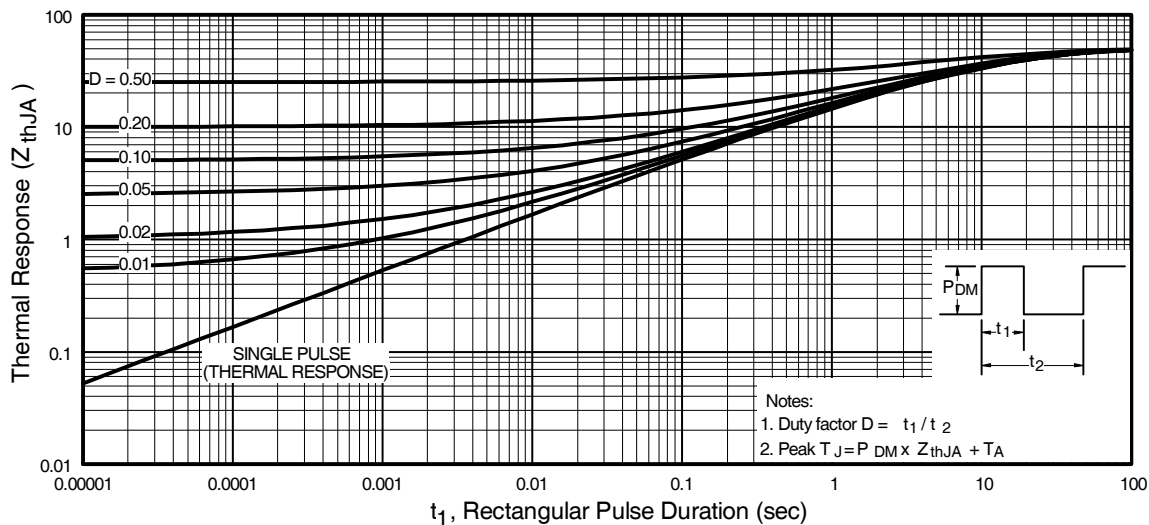
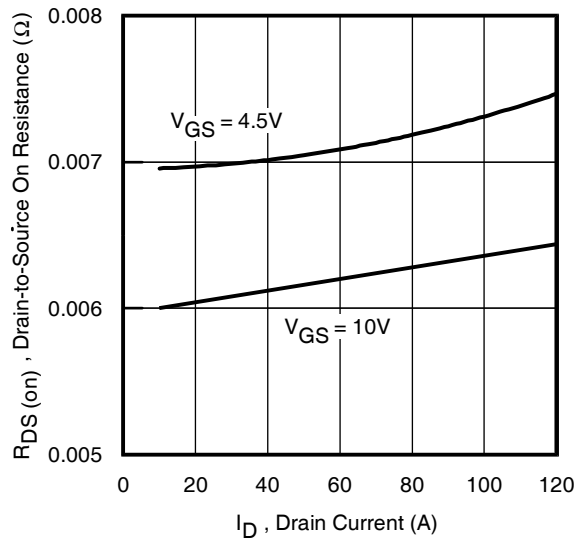
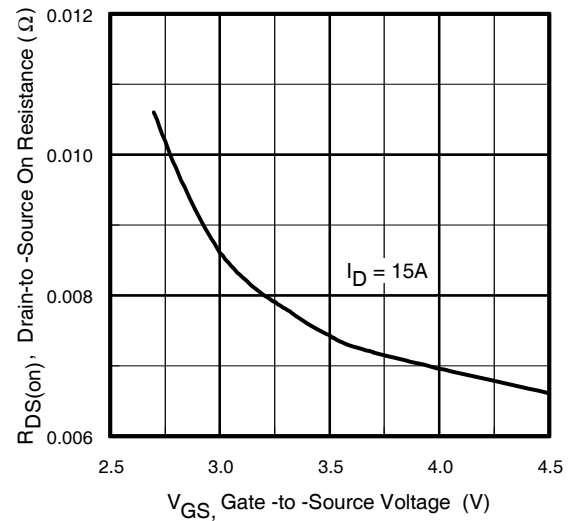
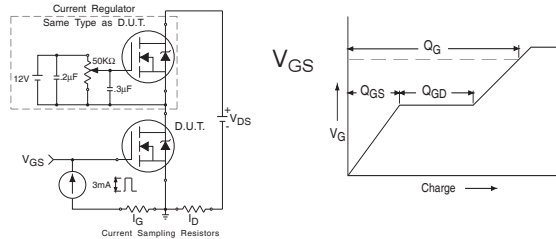
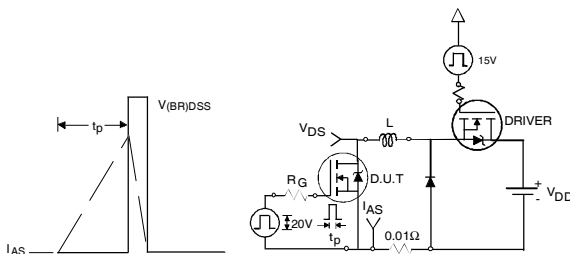
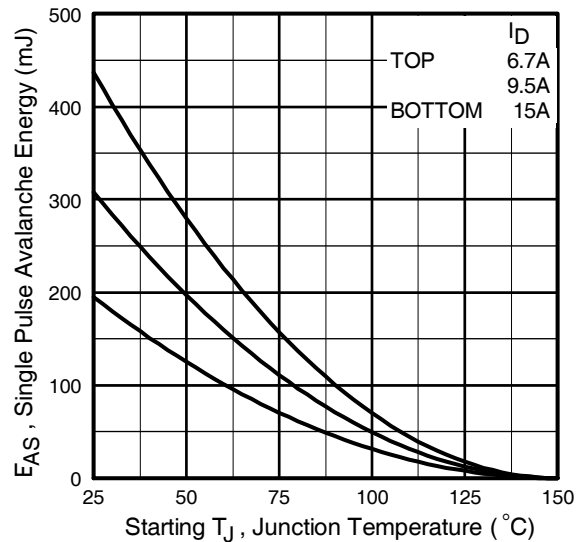
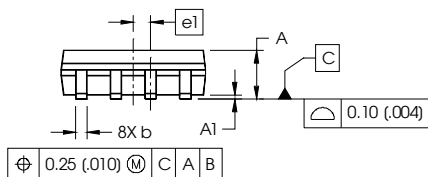


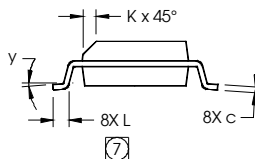
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12. On-Resistance Vs. Drain Current

Fig 13. On-Resistance Vs. Gate Voltage

Fig 13a&b. Basic Gate Charge Test Circuit and Waveform

Fig 14a&b. Unclamped Inductive Test circuit and Waveforms

Fig 14c. Maximum Avalanche Energy Vs. Drain Current

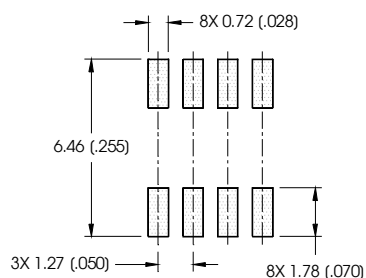
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

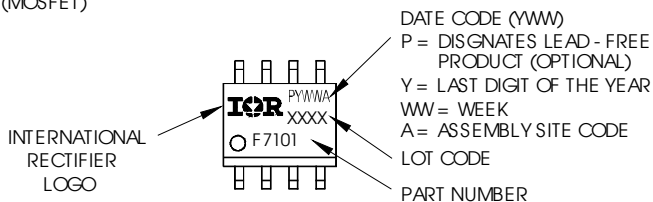


FOOTPRINT



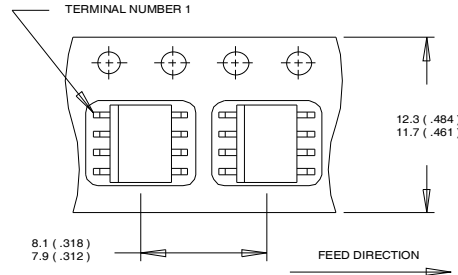
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

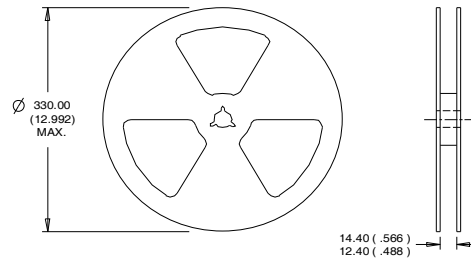


Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

SO-8 Tape and Reel (Dimensions are shown in millimeters (inches))



NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:
 1. CONTROLLING DIMENSION : MILLIMETER.
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Qualification information[†]

Qualification level	Industrial (per JEDEC JESD47F ^{††} guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D ^{††})
RoHS compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

^{††} Applicable version of JEDEC standard at the time of product release

International
 Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
 To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>